I. Nanoelectronics: Process, Device, and Circuit
[10:05–11:45]

1. Analysis of Channel Stress Induced by NiPt-silicide and Its Generation Mechanism [SSDM]  
M. Mizuo (Renesas Semiconductor Engineering Corp.)

2. Isotope Effect on Phonon Thermal Transport in Silicon Nanowires [SSDM]  
J. Hattori (Ritsumeikan Univ.)

3. Impact of Random Telegraph Noise on CMOS Logic Delay Uncertainty under Low Voltage Operation [IEDM]  
T. Matsumoto (Kyoto Univ.)

4. Metal Oxide Nanowires: Synthesis and Memristive Properties [SSDM]  
T. Yanagida (Osaka Univ.)

II. Power and Compound Semiconductor Devices  
[13:00–14:40]

1. GaN Gate Injection Transistor with Integrated Si Schottky Barrier Diode for Highly Efficient DC-DC Converters [IEDM]  
S. Ujita (Panasonic Corp.)

2. Breakdown Characteristics of 12-20 kV-class 4H-SiC PiN Diodes with Improved Junction Termination Structures [ISPSD]  
H. Niwa (Kyoto Univ.)

3. Significant Effect of JFET Doping on Low On-resistance 4H-SiC DMOSFETs of 3300 V Rating [SSDM]  
K. Hamada (Mitsubishi Electric Corp.)

Y. Ando (Renesas Electronics Corp.)

III. Sensor, Solar Cell, and Emerging Devices  
[14:55–16:35]

1. Novel High-sensitivity Broadband Image Sensor with CIGS Thin Films [SSDM]  
Y. Ota (Rohm Co. Ltd.)

K. Kanamoto (Mitsubishi Electric Corp.)

3. Ferroelectric Synapse Device with Brain-like Learning Fuction: Analog Conductance Control in a Ferroelectric-gate Field-effect Transistor Based on the Timing Difference between Two Pulses [SSDM]  
Y. Nishitani (Panasonic Corp.)

4. Development of MWCNT Embedded Micromechanical Resonator Working as Rarefied Gas Sensor [MEMS Conference]  
Y. Isono (Kobe Univ.)